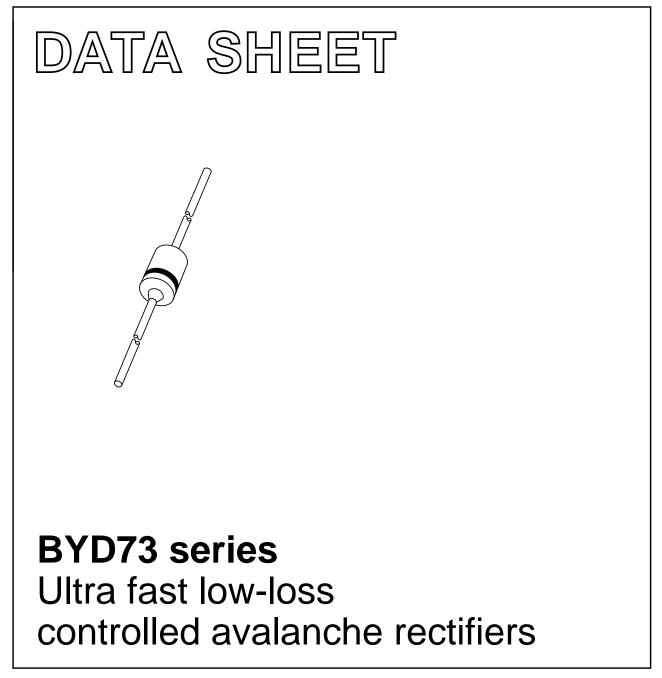
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1996 May 24 1996 Sep 18





FEATURES

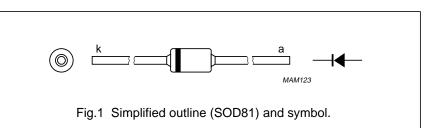
- · Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Cavity free cylindrical glass SOD81 package through Implotec^{™(1)} technology. This package is

hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BYD73A		_	50	V
	BYD73B		-	100	V
	BYD73C		-	150	V
	BYD73D		_	200	V
	BYD73E		_	250	V
	BYD73F		_	300	V
	BYD73G		_	400	V
V _R	continuous reverse voltage				
	BYD73A		-	50	V
	BYD73B		_	100	V
	BYD73C		_	150	V
	BYD73D		_	200	V
	BYD73E		_	250	V
	BYD73F		_	300	V
	BYD73G		_	400	V
I _{F(AV)}	average forward current	T _{tp} = 55 °C; lead length = 10 mm;			
	BYD73A to D	see Figs 2 and 3;	_	1.75	A
	BYD73E to G	averaged over any 20 ms period; see also Figs 10 and 11	-	1.70	A
I _{F(AV)}	average forward current	T _{amb} = 60 °C; PCB mounting (see			
	BYD73A to D	Fig.16); see Figs 4 and 5;	_	1.00	A
	BYD73E to G	averaged over any 20 ms period; see also Figs 10 and 11	_	0.95	A

Product specification

BYD73 series

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BYD73 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{FRM}	repetitive peak forward current	$T_{tp} = 55 \ ^{\circ}C$; see Figs 6 and 7			
	BYD73A to D		-	14	А
	BYD73E to G		-	15	А
I _{FRM}	repetitive peak forward current	$T_{amb} = 60 \ ^{\circ}C$; see Figs 8 and 9			
	BYD73A to D		-	8.5	А
	BYD73E to G		-	9.5	А
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave;	-	25	А
		$T_j = T_{j \max}$ prior to surge;			
		$V_{R} = V_{RRMmax}$			
E _{RSM}	non-repetitive peak reverse	L = 120 mH; $T_j = T_{j max}$ prior to	-	10	mJ
	avalanche energy	surge; inductive load switched off			
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		-65	+175	°C

ELECTRICAL CHARACTERISTICS

 T_j = 25 $^\circ C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 A; T_j = T_{j max};$				
	BYD73A to D	see Figs 12 and 13	_	-	0.75	V
	BYD73E to G		_	-	0.83	V
V_{F}	forward voltage	I _F = 1 A;				
	BYD73A to D	see Figs 12 and 13	_	-	0.98	V
	BYD73E to G		_	-	1.05	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA				
	BYD73A		55	-	-	V
	BYD73B		110	_	-	V
	BYD73C		165	-	-	V
	BYD73D		220	-	-	V
	BYD73E		275	-	-	V
	BYD73F		330	-	-	V
	BYD73G		440	-	-	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.14	_	_	1	μA
		$V_R = V_{RRMmax};$ T _j = 165 °C; see Fig.14	_	-	100	μA
t _{rr}	reverse recovery time	when switched from				
	BYD73A to D	$I_F = 0.5 \text{ A to } I_R = 1 \text{ A};$	_	_	25	ns
	BYD73E to G	measured at I _R = 0.25 A; see Fig.18	_	_	50	ns

BYD73 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C _d	diode capacitance	f = 1 MHz; V _R = 0 V;				
	BYD73A to D	see Fig.15	_	50	_	pF
	BYD73E to G		_	40	_	pF
$\left \frac{dI_R}{dt} \right $	maximum slope of reverse recovery current BYD73A to D	when switched from $I_F = 1 A$ to $V_R \ge 30 V$ and $dI_F/dt = -1 A/\mu s$; see Fig.17	_	_	4	A/µs
	BYD73E to G		-	_	5	A/µs

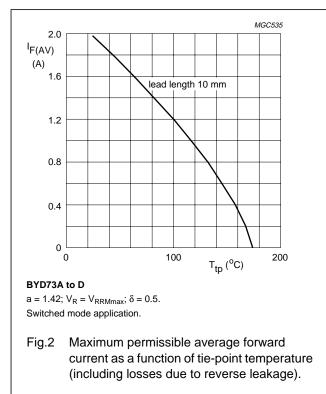
THERMAL CHARACTERISTICS

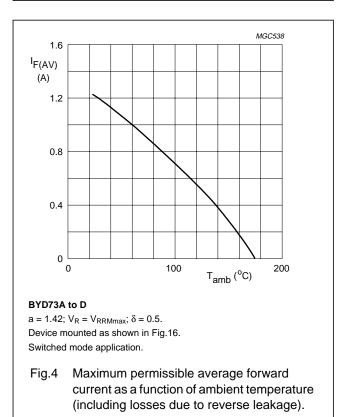
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	120	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.16. For more information please refer to the *"General Part of associated Handbook".*

GRAPHICAL DATA





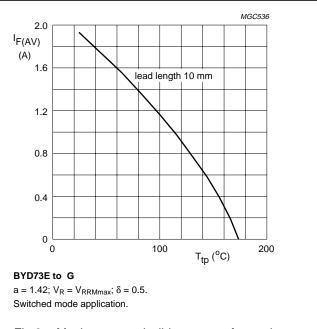


Fig.3 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

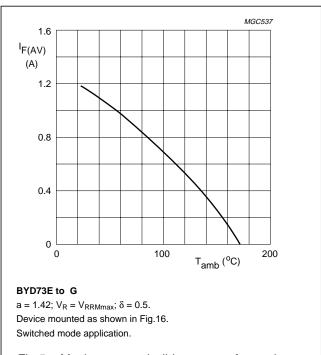


Fig.5 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

BYD73 series

BYD73 series

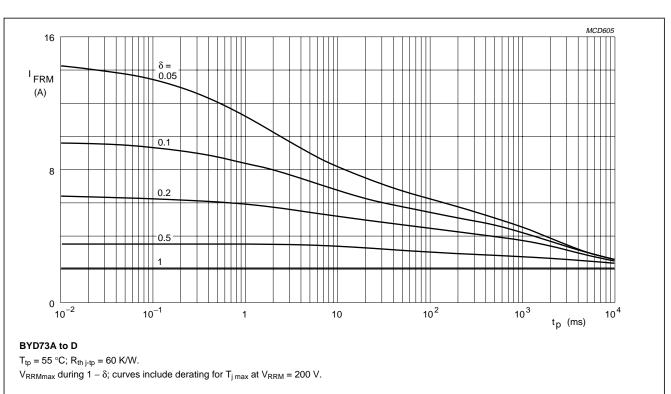


Fig.6 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

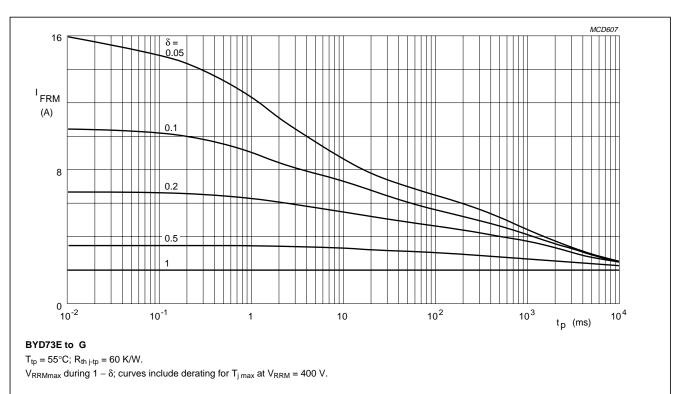


Fig.7 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

BYD73 series

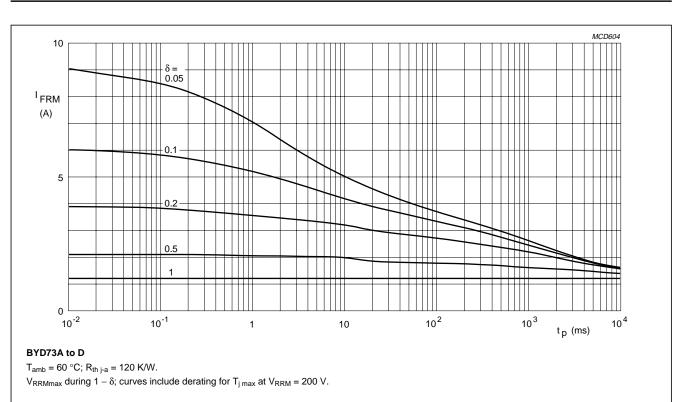


Fig.8 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

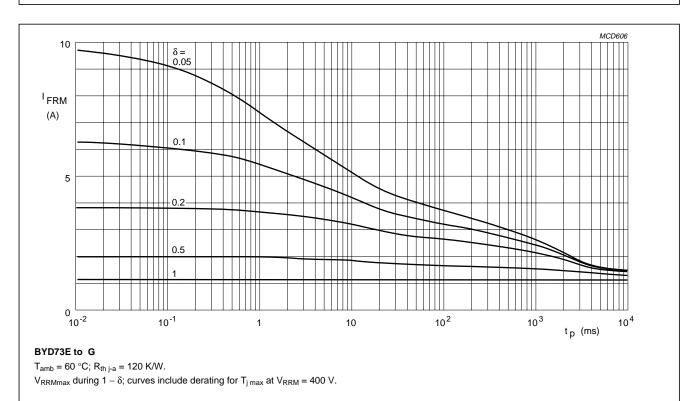


Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

BYD73 series

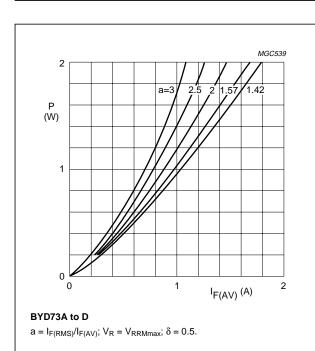
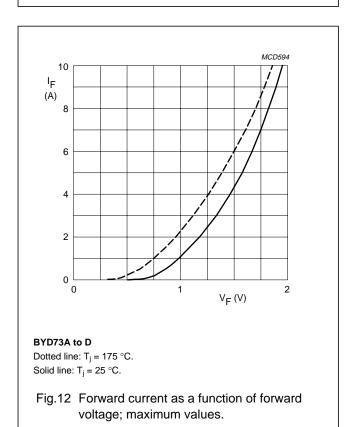
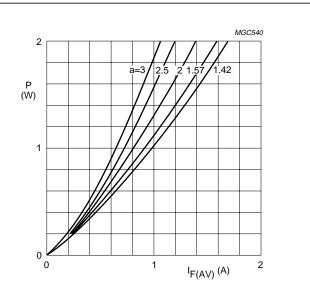


Fig.10 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.





BYD73E to G

 $a = I_{F(RMS)}/I_{F(AV)}; V_{R} = V_{RRMmax}; \delta = 0.5.$

Fig.11 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

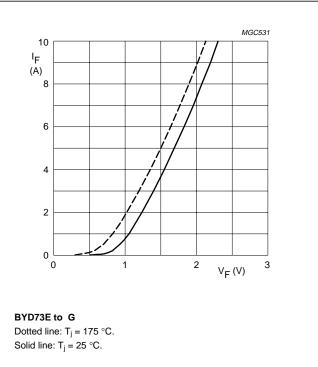
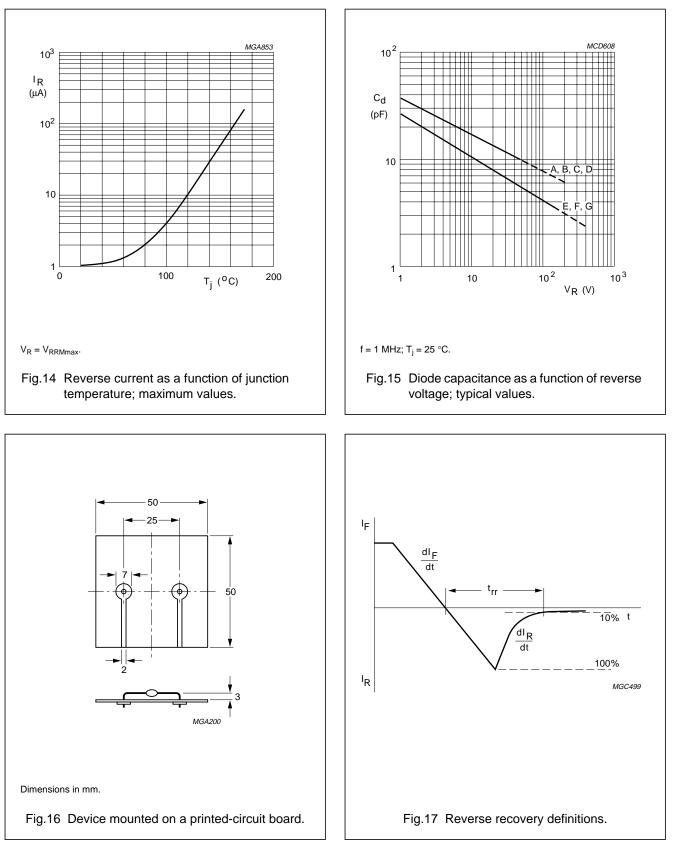
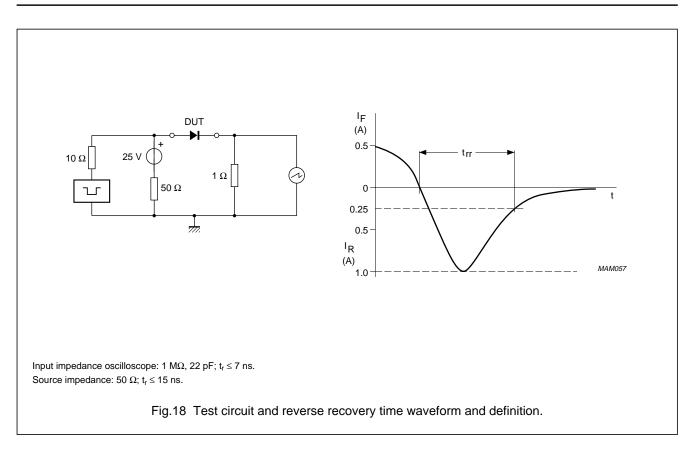


Fig.13 Forward current as a function of forward voltage; maximum values.

BYD73 series

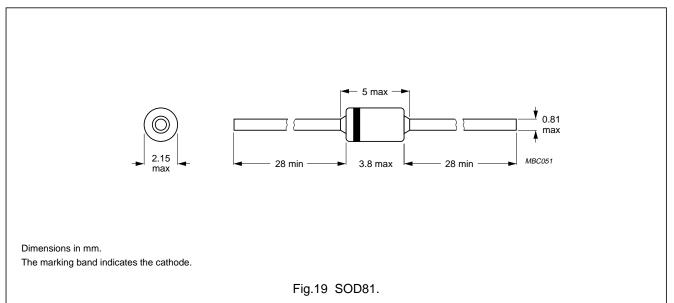


BYD73 series



BYD73 series

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.